

NCE N-Channel Super Trench II Power MOSFET

Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

- DC/DC Converter
- ●Ideal for high-frequency switching and synchronous rectification

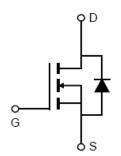
General Features

- V_{DS} =100V, I_D =230A $R_{DS(ON)}$ =2.15m Ω , typical@ V_{GS} =10V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!

TO-247





Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP026N10T	NCEP026N10T	TO-247	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	230	А
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	165	А
Pulsed Drain Current	I _{DM}	920	Α
Maximum Power Dissipation	P _D	300	W
Derating factor		2	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	2300	mJ
Operating Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 To 175	$^{\circ}$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{ heta JC}$	0.5	°C/W	
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Electrical Characteristics (T_C=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	<u> </u>					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	V _{GS} =0V I _D =250μA 100		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V	0V,V _{GS} =0V -		1	μΑ
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	<u> </u>					
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2.0	3.0	4.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =115A	-	2.15	2.6	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =115A		90	-	S
Dynamic Characteristics (Note4)	<u> </u>		•			
Input Capacitance	C _{lss}		-	14000	-	PF
Output Capacitance	C _{oss}	V _{DS} =50V,V _{GS} =0V, F=1.0MHz		1100	-	PF
Reverse Transfer Capacitance	C _{rss}	r=1.0lVlm2	-	60	-	PF
Switching Characteristics (Note 4)	<u> </u>					
Turn-on Delay Time	t _{d(on)}		-	34	-	nS
Turn-on Rise Time	t _r	V_{DD} =50 V , I_{D} =115 A	-	27	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =1.6 Ω	-	78	-	nS
Turn-Off Fall Time	t _f		-	30	-	nS
Total Gate Charge	Qg	V -F0V/I -400A	-	240	-	nC
Gate-Source Charge	Q _{gs}	$V_{DS}=50V,I_{D}=100A,$	-	62		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	73		nC
Drain-Source Diode Characteristics	<u> </u>					
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =115A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	200	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 115A	-	101	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	280	-	nC

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}\text{C}$,V $_{\text{DD}}$ =50 V,V $_{\text{G}}$ =10 V,L=0.5 mH,Rg=25 Ω





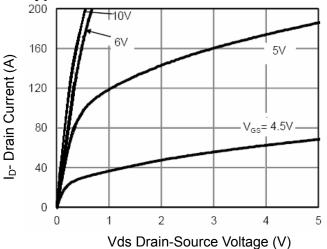


Figure 1 Output Characteristics

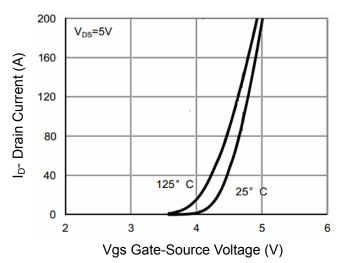


Figure 2 Transfer Characteristics

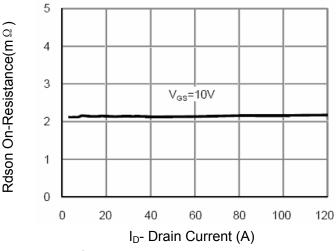


Figure 3 Rdson- Drain Current

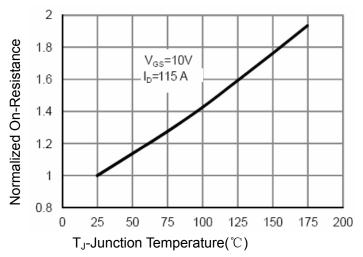


Figure 4 Rdson-Junction Temperature

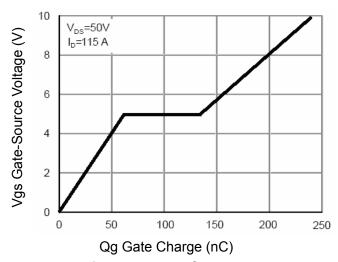


Figure 5 Gate Charge

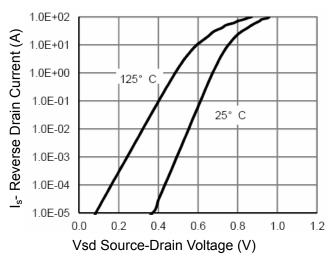


Figure 6 Source- Drain Diode Forward



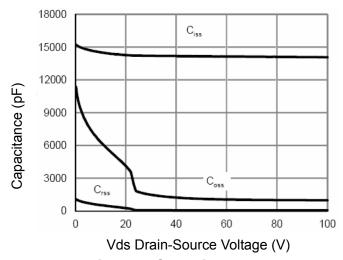


Figure 7 Capacitance vs Vds

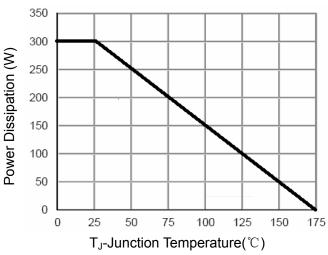


Figure 9 Power De-rating

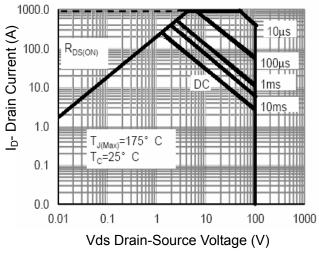


Figure 8 Safe Operation Area

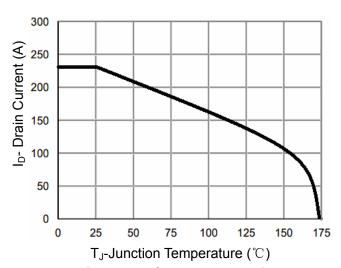


Figure 10 Current De-rating

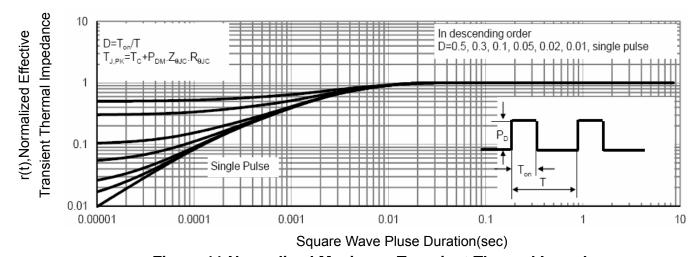
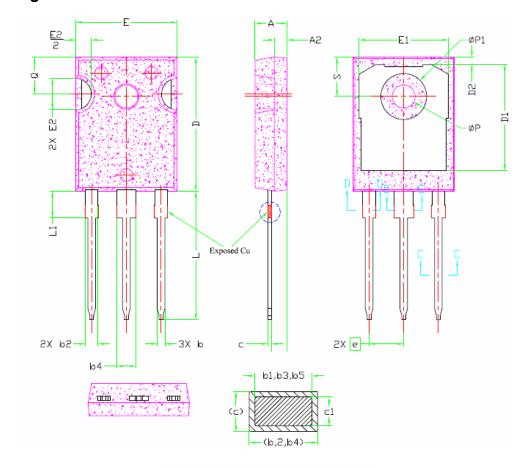


Figure 11 Normalized Maximum Transient Thermal Impedance



TO-247 Package Information



01/11/01		HOTES		
SYMBOL	MIN.	NOM.	MAX.	NOTES
Α	4.83	5.02	5.21	
A1	2,29	2.41	2,55	
A2	1,50	2.00	2.49	
ь	1.12	1.20	1,33	
b1	1.12	1.20	1.28	
b2	1.91	2.00	2.39	6
b3	1.91	2.00	2.34	
b4	2.87	3.00	3.22	6,8
b5	2.87	3.00	3.18	
С	0.55	0.60	0.69	6
c1	0.55	0.60	0.65	
D	20,80	20,95	21,10	4
D1	16,25	16,55	17,65	5
D2	0,51	1,19	1,35	
E	15,75	15.94	16,13	4
E1	13,46	14.02	14.16	5
E2	4.32	4.91	5.49	3
e	5.44BSC			
L	19.81	20.07	20,32	
L1	4.10	4.19	4.40	6
ØP	3.56	3.61	3.65	7
ØP1	7.19REF			
Q	5,39	5.79	6.20	
S	6.04	6.17	6.30	



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